



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Features

- Low On-Resistance:
 $R_{DS(ON)} < 88m\Omega @ V_{GS} = 4.5V$
 $R_{DS(ON)} < 138m\Omega @ V_{GS} = 2.5V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage

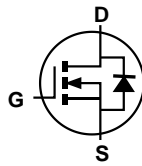
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Alloy 42
Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

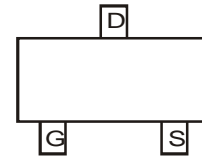
SOT323



Top View



Internal Schematic



Pin Configuration

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	28	V
Gate-Source Voltage	V_{GSS}	± 12	V
Drain Current (Note 5)	I_D	$T_A = +25^\circ\text{C}$	1.6
		$T_A = +70^\circ\text{C}$	1.2
Drain Current (Note 5)	Pulsed I_{DM}	6.4	A
Body-Diode Continuous Current (Note 5)	I_S	1.5	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	350	mW
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5)	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	28	—	—	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	800	nA	$V_{DS} = 28V, V_{GS} = 0V$
Gate-Body Leakage	I_{GSS}	—	—	± 80 ± 800	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 19V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.62	0.94	1.4	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	73	88	$m\Omega$	$V_{GS} = 4.5V, I_D = 1.6A$
		—	115	138		$V_{GS} = 2.5V, I_D = 1.2A$
Forward Transconductance	$ Y_{fs} $	—	5.4	—	S	$V_{DS} = 5V, I_D = 2.7A$
Source-Drain Diode Forward Voltage	V_{SD}	—	—	1.16	V	$V_{GS} = 0V, I_S = 1.5A$
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	305	—	pF	$V_{DS} = 5V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	74	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	48	—	pF	

- Notes:
- Device mounted on 1in^2 FR-4 PCB on 2oz. Copper. $t \leq 10$ sec.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

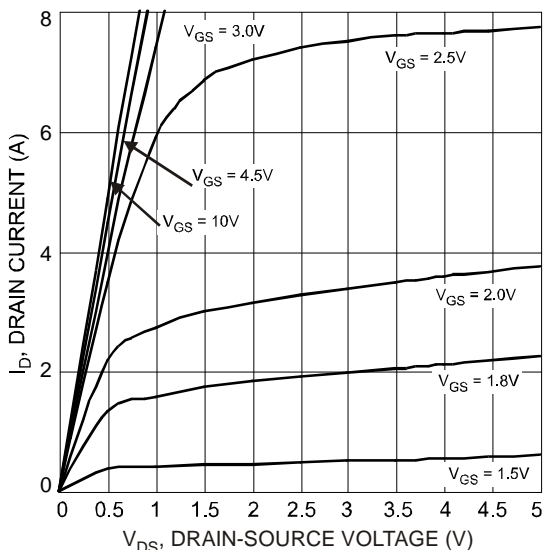


Fig. 1 Typical Output Characteristics

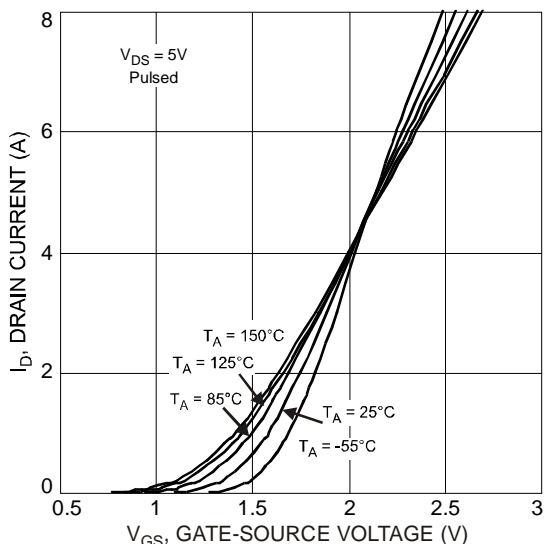


Fig. 2 Typical Transfer Characteristics

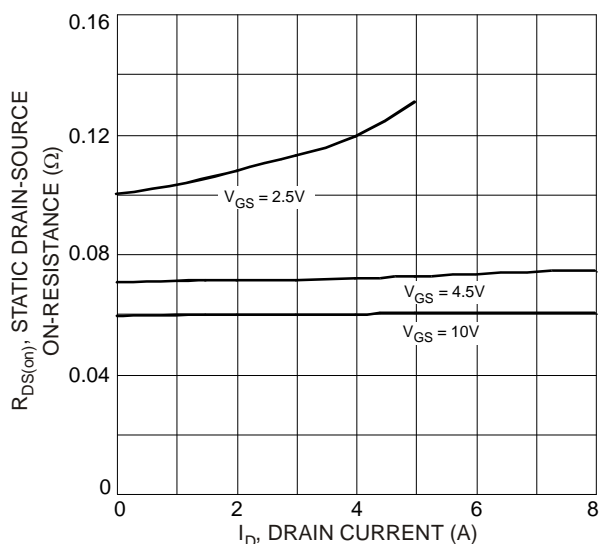


Fig. 3 On-Resistance vs. Drain Current and Gate Voltage

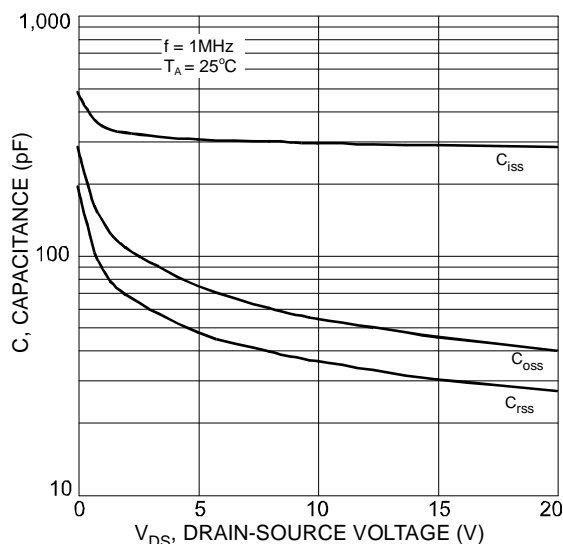


Fig. 4 Typical Total Capacitance

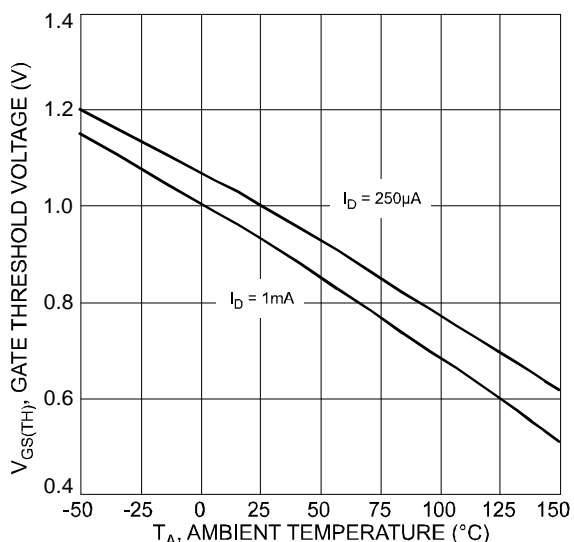


Fig. 5 Gate Threshold Voltage vs. Ambient Temperature

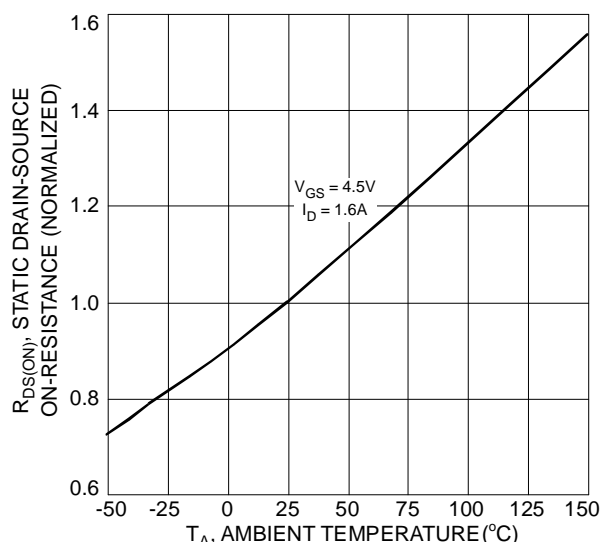


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

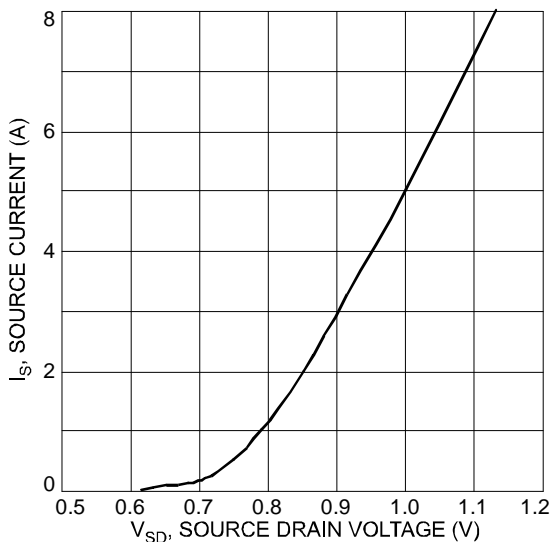
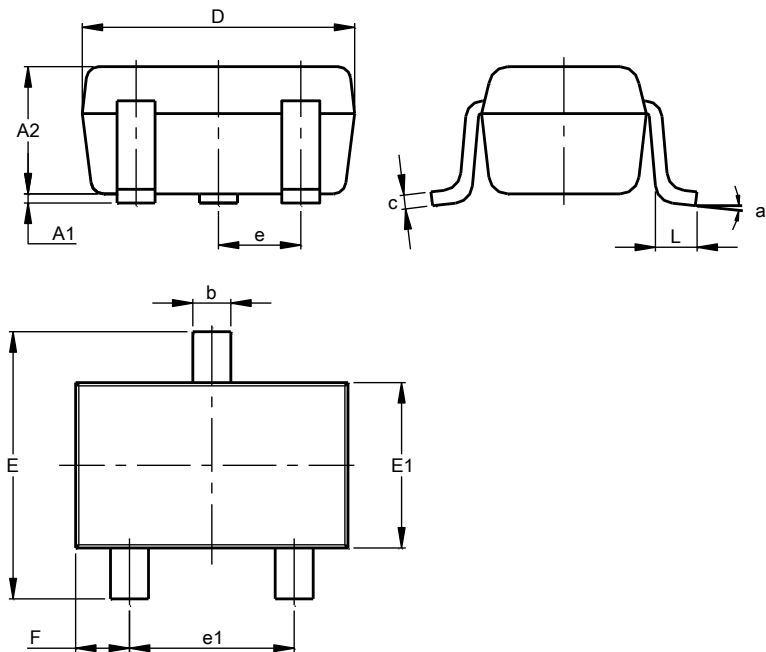


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

Package Outline Dimensions

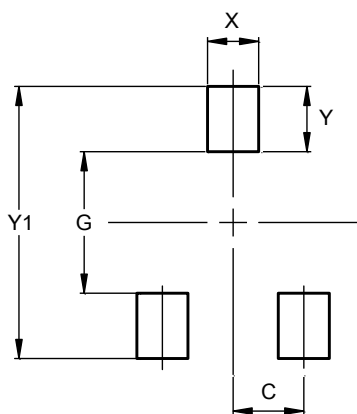
SOT323



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	8°		
All Dimensions in mm			

Suggested Pad Layout

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500